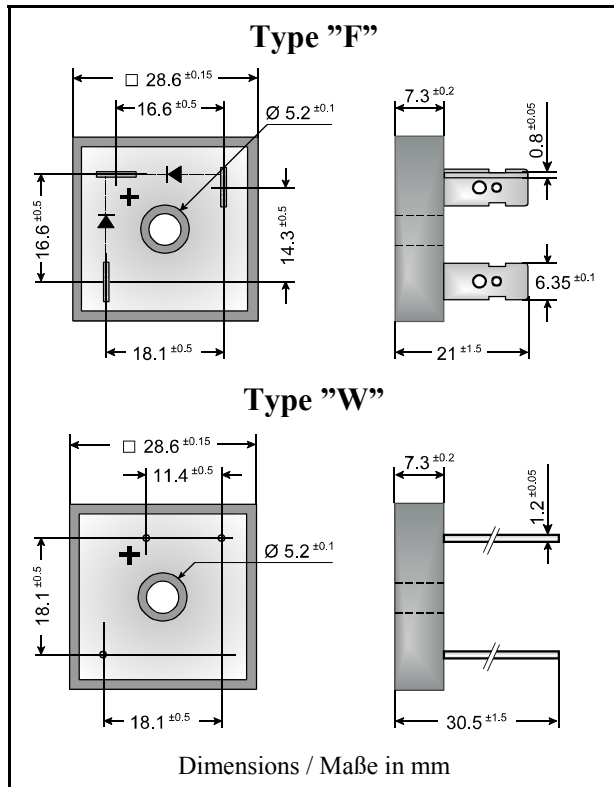


Silicon-Twin Rectifiers
Center tap

Silizium-Doppeldioden
Mittelpunktschaltung



Nominal current 30 A
Nennstrom

Alternating input voltage 60...250 V
Eingangswchelsspannung

Plastic case with alu-bottom
Kunststoffgehäuse mit Alu-Boden

Dimensions 28.6 x 28.6 x 7.3 [mm]
Abmessungen

Weight approx. 23 g
Gewicht ca.

Recognized Product – UL-File E175067
Anerkanntes Produkt – UL Nr. E175067

Compound has classification UL94V-0
Vergußmasse UL94V-0 klassifiziert

Standard packaging: bulk see page 22
Standard Lieferform: lose im Karton s.S. 22

Maximum ratings

Grenzwerte

Type Typ	max. alternating input voltage max. Eingangswchelspannung V_{VRMS} [V]	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] ¹⁾
D30 VC20 F/W	60	200
D30 VC40 F/W	120	400
D30 VC60 F/W	190	600
D30 VC80 F/W	250	800

Repetitive peak fwd. current – Period. Spitzenstrom	$f > 15$ Hz	I_{FRM}	80 A ²⁾
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwell	$T_A = 25^\circ\text{C}$	I_{FSM}	300 A
Rating for fusing – Grenzlastintegral, $t < 10$ ms	$T_A = 25^\circ\text{C}$	i^2t	450 A ² s
Isolation voltage – Isolationsspannung	$t = 1$ min	V_{ISO}	> 2000 V
Operating junction temperature – Sperrschichttemperatur		T_j	$-50 \dots +150^\circ\text{C}$
Storage temperature – Lagerungstemperatur		T_s	$-50 \dots +150^\circ\text{C}$

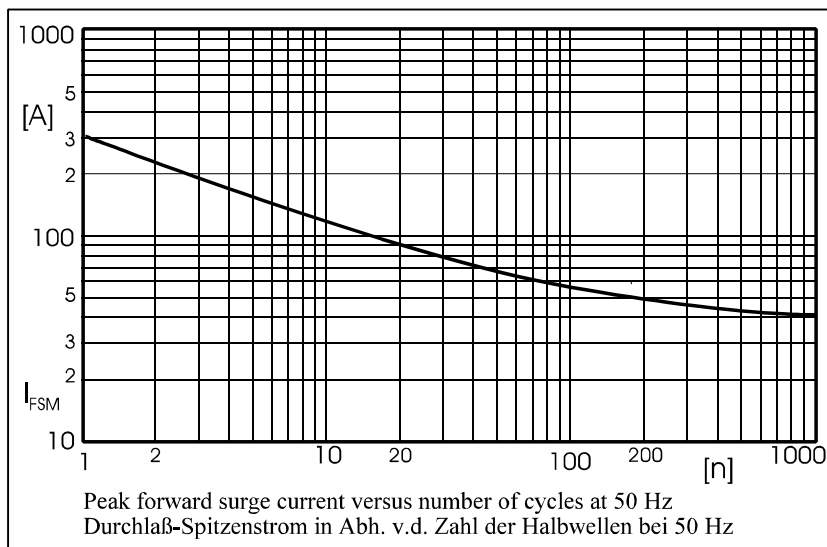
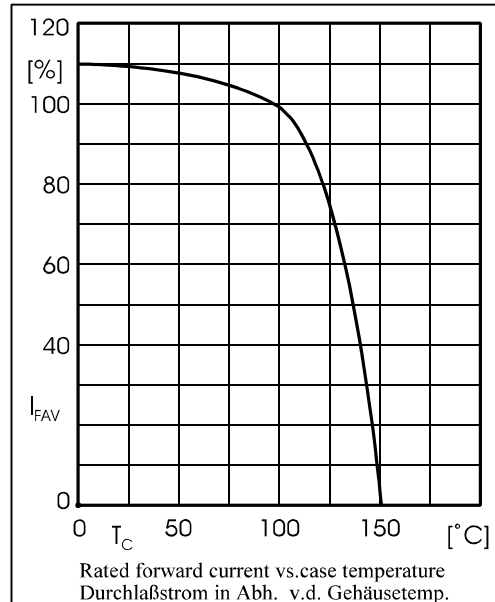
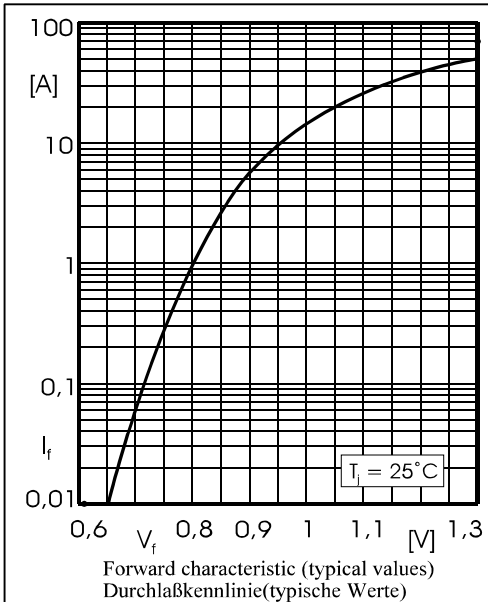
¹⁾ Valid per diode – Gültig pro Diode

²⁾ Max. case temperature $T_C = 100^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 100^\circ\text{C}$

Characteristics

Kennwerte

Max. current with cooling fin 300 cm ² Dauergrenzstrom mit Kühlblech 300 cm ²	$T_A = 50^\circ\text{C}$	R-load C-load	I_{FAV} I_{FAV}	30.0 A 26.0 A
Forward voltage – Durchlaßspannung	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$	V_F	< 1.05 V ¹⁾
Leakage current – Sperrstrom	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	I_R	< 25 μA
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			R_{thC}	< 1.0 K/W
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		18 ± 10% lb.in 2 ± 10% Nm



¹⁾ Valid per diode – Gültig pro Diode